

Dual N-channel 60 V, 10 mΩ standard level MOSFET

2 September 2015

Product data sheet

1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	40	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	64	W
Static chara	cteristics FET1 and FET2						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11		-	8	10	mΩ
Dynamic cha	aracteristics FET1 and FE	T2					
Q _{GD}	gate-drain charge	$I_{D} = 10 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 10 \text{ V};$ $T_{j} = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	9.7	-	nC

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2	\bigcirc	
4	G2	gate2		
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	(0011200)	

6. Ordering information

Table 3. Ordering information								
Type number	Package	kage						
	Name	Description	Version					
BUK7K13-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205					

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7K13-60E	71360E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	60	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	64	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	40	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>		-	38	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 3		-	213	А
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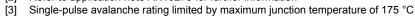
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	diode FET1 and FET2		1			
I _S	source current	T _{mb} = 25 °C	[1]	-	40	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	213	А
Avalanche Ru	uggedness FET1 and FET2		1			
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 40 \text{ A}; V_{sup} \leq 60 V; \text{R}_{GS} = 50 \Omega; \\ V_{GS} &= 10 V; \text{T}_{j(init)} = 25 ^{\circ}\text{C}; \text{unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[2][3]	-	82	mJ

[1] Continuous current is limited by package.

[2] Refer to application note AN10273 for further information



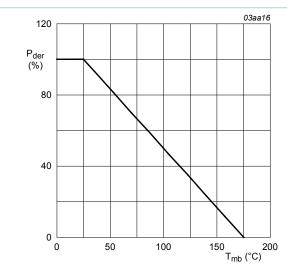
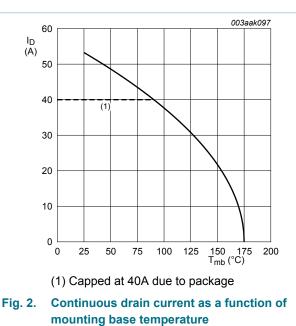


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

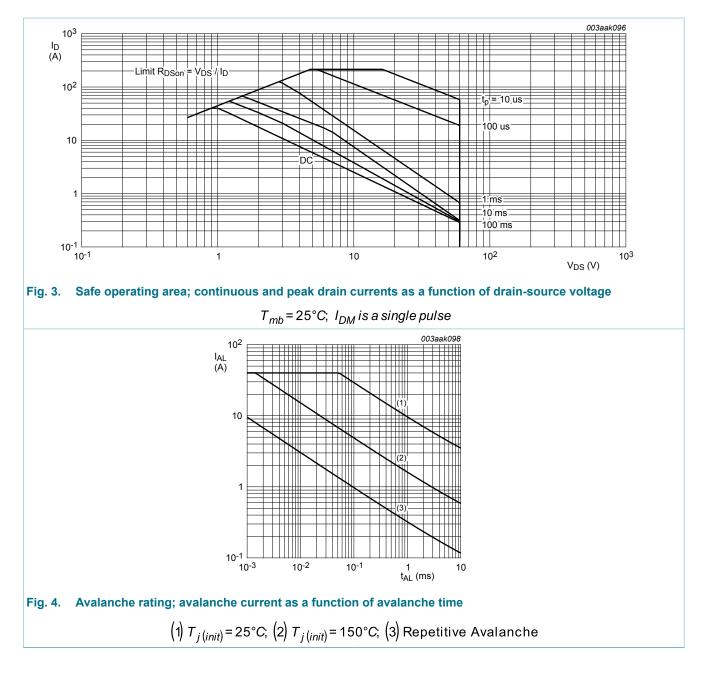


 $V_{GS} \ge 10V$

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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	2.36	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

Table 6. Thermal characteristics

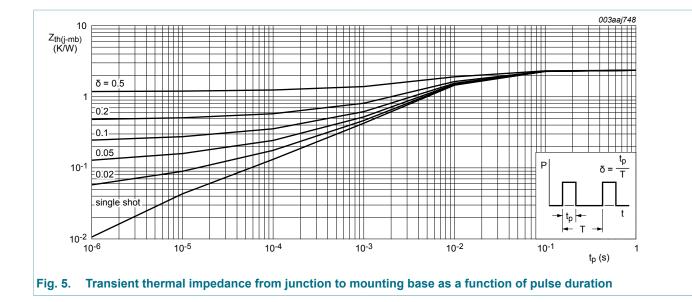
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10. Characteristics

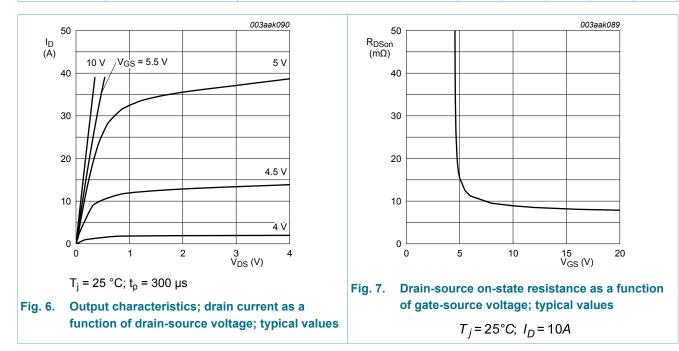
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics FET1 and FET2		I				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V	
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V	
V _{GS(th)} gate-source thresho voltage	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V	
			$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA	
			V_{DS} = 60 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS} gate leakage	I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11	-	8	10	mΩ	
		V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12	-	18	22	mΩ	
Dynamic ch	aracteristics FET1 and FE	T2		_			
Q _{G(tot)}	total gate charge	I_D = 10 A; V_{DS} = 48 V; V_{GS} = 10 V;	-	30.1	-	nC	
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	6.7	-	nC	
Q _{GD}	gate-drain charge		-	9.7	-	nC	

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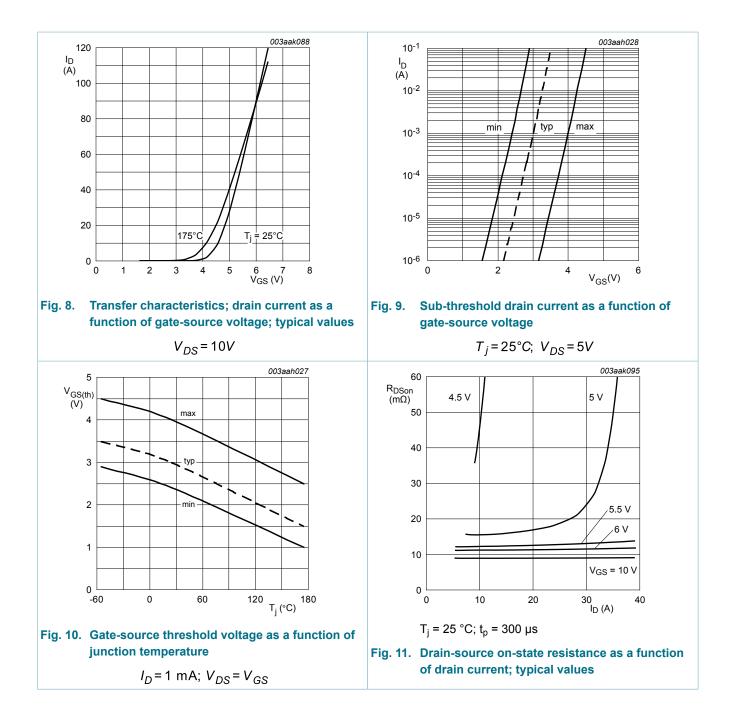
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>		-	1622	2163	pF
C _{oss}	output capacitance			-	229	275	pF
C _{rss}	reverse transfer capacitance			-	143	196	pF
t _{d(on)}	turn-on delay time	V_{DS} = 48 V; R_{L} = 5 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C		-	8.4	-	ns
t _r	rise time			-	11.4	-	ns
t _{d(off)}	turn-off delay time			-	20.4	-	ns
t _f	fall time	-		-	13.6	-	ns
Source-drain	diode FET1 and FET2	I	1				,
V _{SD}	source-drain voltage	I_{S} = 10 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.78	1.2	V
t _{rr}	reverse recovery time	I_{S} = 10 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;		-	25.6	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C		-	23.5	-	nC

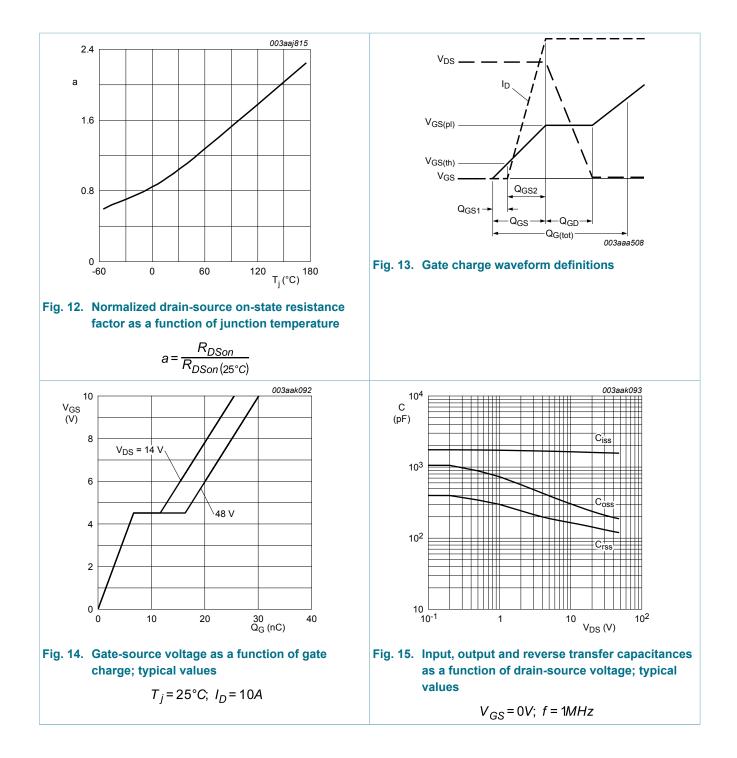


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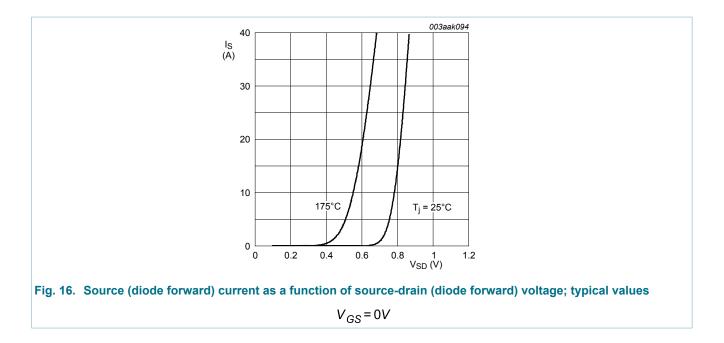


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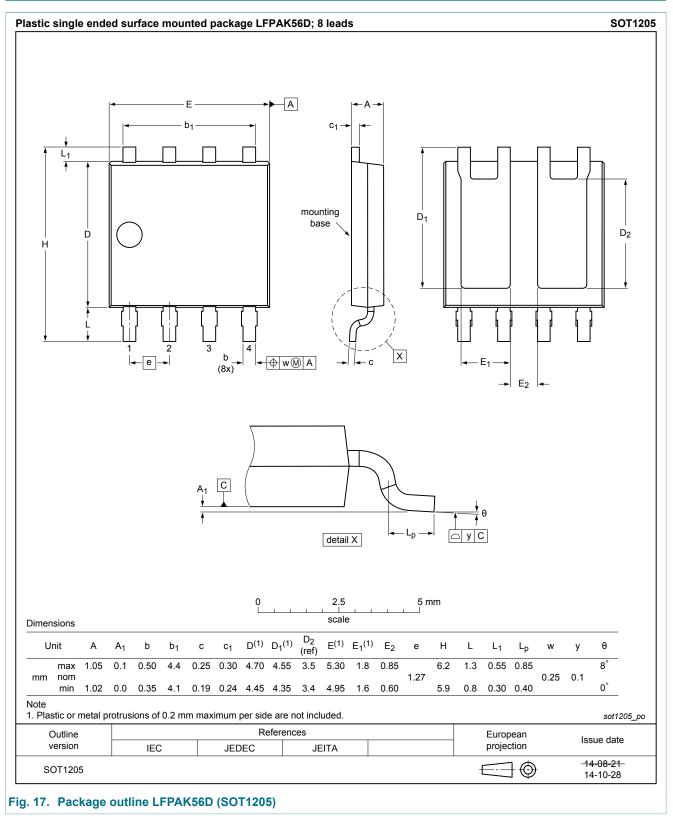
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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